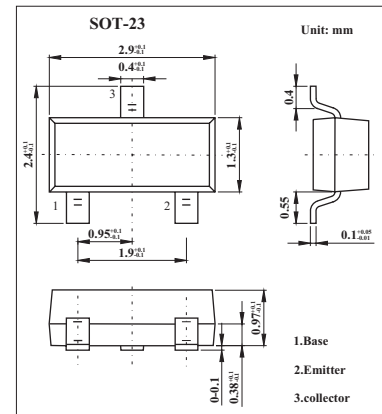


PNP Transistors

KST8550S

■ Features

- Collector current: $I_c = -0.5A$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_c	-0.5	A
Collector Power Dissipation	P_c	0.3	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_c = -100 \mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_c = -1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_c = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3V, I_c = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_c = -50mA$	120		350	
		$V_{CE} = -1V, I_c = -500mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -500mA, I_B = -50mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = -500mA, I_B = -50mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -6V, I_c = -20mA, f = 30MHz$	150			MHz

■ hFE Classification

Marking	2TY	
Rank	L	H
hFE	120~200	200~350

KST8550S

■ Typical Characteristics

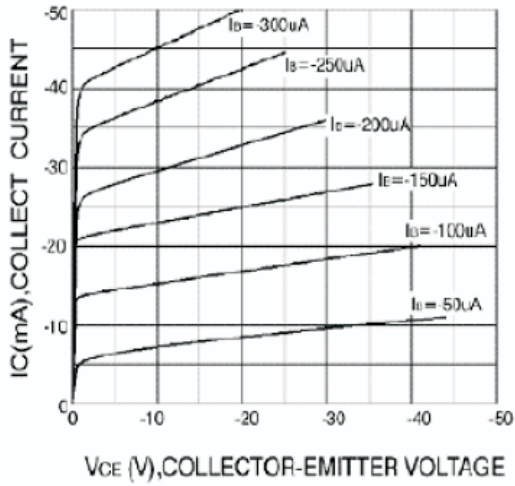


Fig.1 Static Characteristic

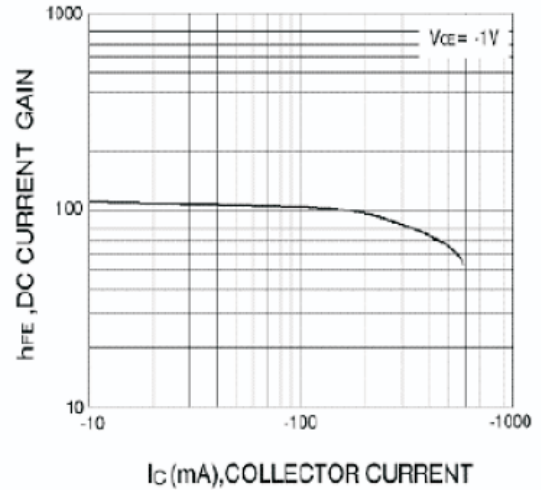


Fig.2 DC Current Gain

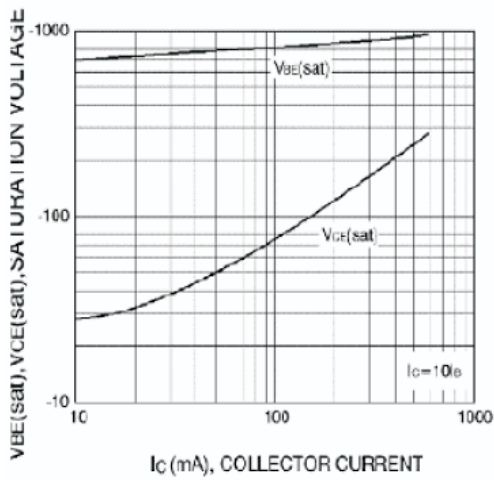


Fig.3 Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

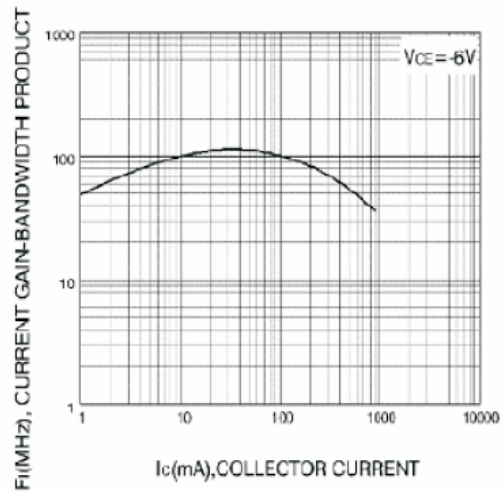


Fig.4 Current Gain Bandwidth Product